

**AMENDMENTS TO THE SPECIFICATION:**

*Please amend the paragraph of the specification beginning at page 21, line 19, and continuing to page 22, line 9, as follows:*

The nonvolatile variable resistor R<sub>v</sub> is formed on a substrate (not shown) and the first electrode 1 and the second electrode 3 are formed on the substrate so that a major dimension (height "h") of the first electrode 1 and a major dimension (height "h") of the second electrode 3 as to are perpendicular to the substrate and face each other in a direction of a surface of the substrate. In a case where scaling applied to reduce a projected area on a plane of the nonvolatile variable resistor R<sub>v</sub> with the nonvolatile variable resistor R<sub>v</sub> in a three-dimensional structure as described above, an increase in resistance of the nonvolatile variable resistor R<sub>v</sub> can be suppressed. That is, there occurs no increase in resistance accompanied by reduction of a surface area of the first electrode 1 due to scaling, which occurs otherwise in a conventional technique. Note that by using the nonvolatile variable resistor R<sub>v</sub> according to the first embodiment in a memory device (memory cell), there can be realized a memory device with a large capacity, in which no reduction in operating speed occurs due to scaling.